

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-30V	38mΩ@-10V	-5.8A
	58mΩ@-4.5V	

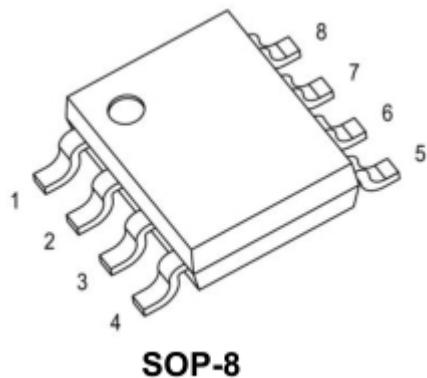
Feature

- TrenchFET Power MOSFET
- Excellent RDS(on) and Low Gate Charge

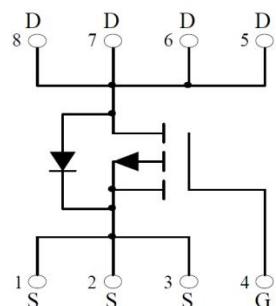
Application

- Load Switch for Portable Devices
- Battery Switch

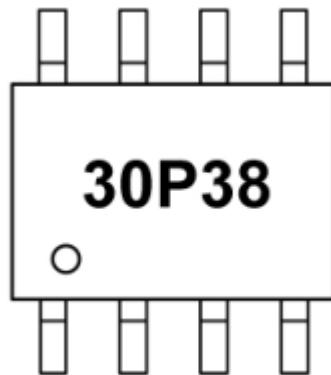
Package



Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-5.8	A
Plused Drain Current	I_{DM}	-25	A
Power Dissipation	P_D	1.5	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	89	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

Electrical characteristics

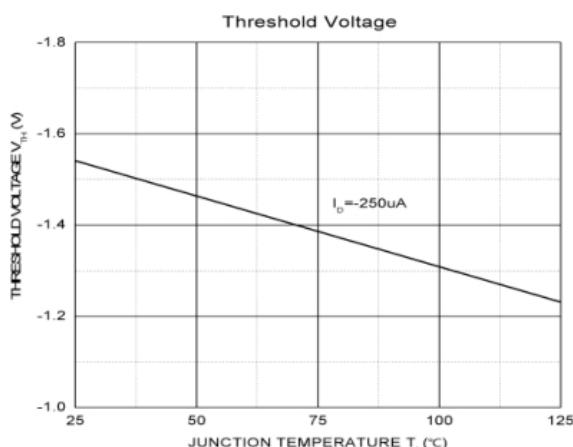
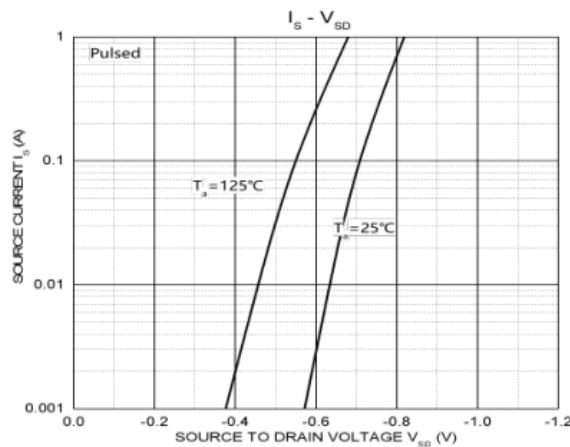
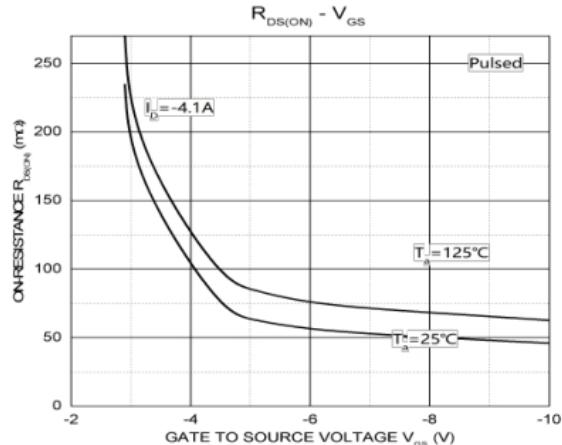
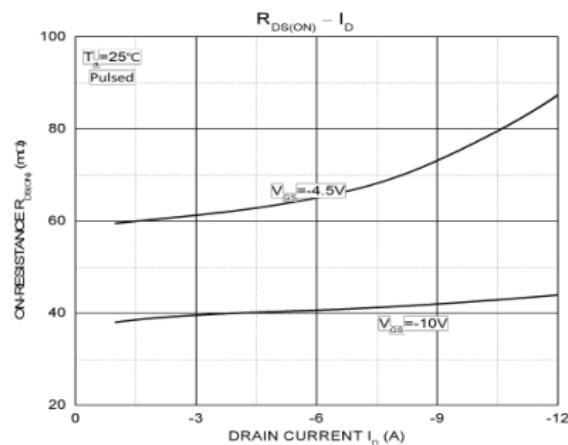
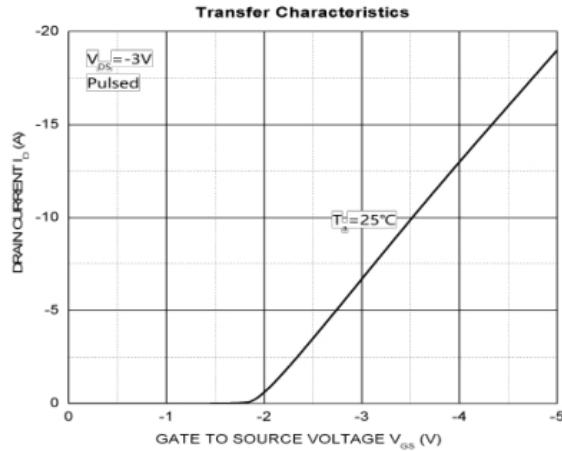
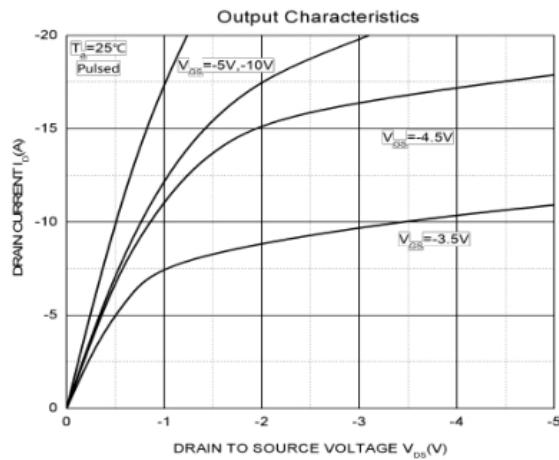
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Off characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-30.5			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24\text{V}, V_{GS} = 0\text{V}$			-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
On characteristics²⁾						
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1.0	-1.5	-2.5	V
Drain-Source On-Resistance ¹	$R_{DS(\text{on})}$	$V_{GS} = -10\text{V}, I_D = -4.1\text{A}$		38	50	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -3\text{A}$		58	80	
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -15\text{V}, I_D = -4.6\text{A}, V_{GS} = -10\text{V},$			40	nC
Gate-Source Charge	Q_{gs}			4		
Gate-Drain Charge	Q_{gd}			6.3		
Turn-on Delay Time	$T_{d(\text{on})}$	$V_{DD} = -15\text{V}, I_D = -1\text{A}, V_{GS} = -10\text{V}, R_G = 6\Omega, R_L = 15\Omega,$			30	nS
Turn-on Rise Time	T_r				60	
Turn-off Delay Time	$T_{d(\text{off})}$				120	
Turn-off Fall Time	T_f				100	
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$I_{SD} = -2.6\text{A}, V_{GS} = 0\text{V}$			-1.2	V

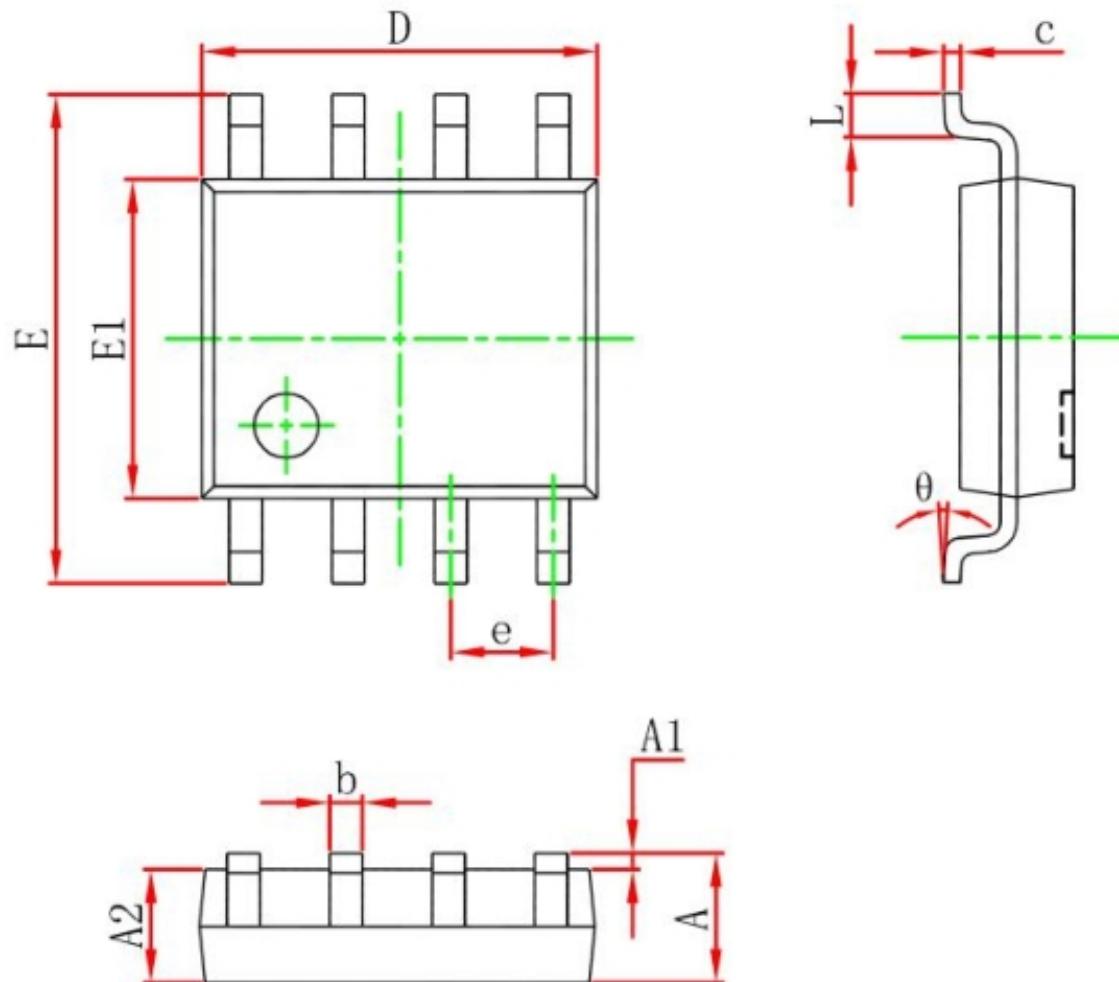
Notes:

1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

Typical Characteristics



SOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°